ANL

assemble

baking (220°C, 24h)

falling temperature

Oxygen Plasma

Sb (25°C)

Oxygen Plasma

Sb (25°C)

baking (150°C, 1h)

K (150°C)

Cs (150°C)

Prototype

IHEP

assemble

baking (220°C, 24h)

falling temperature

Oxygen Plasma

Sb (25°C)

baking (210°C, 1h)

K (200°C)

Cs (180°C)

baking (210°C, 2h)

Prototype
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| Oxygen Plasma | ✓Pressure of the oxygen: **0.3 torr**  
✓The voltage to the glass: **20K**  
✓Shape of the electrode: **tip** | ✓Pressure of the oxygen: **10^{-2} torr**  
✓The voltage to the glass: **700V**  
✓Shape of the electrode: **planate** |
| Sb | ✓Wire material: **Pt-Mo**  
✓Monitor the reflection light by the Photodiode | ✓Wire material: **Ni**  
✓Look at by eyes |
| K | ✓Outgas with small current (2A) during the baking time;  
✓Monitor the photo response current, till the increasing trend stops  
✓Continue the evaporation until photo current drops to 80% of the Max. value; | ✓Outgas with the high frequency gun before baking;  
✓Monitor the photo response current, till the increasing trend stops; |
| Cs | ✓Outgas with small current (2A) during the baking time;  
✓Monitor the photo response current, after the increasing trend stops, continue evaporation until the current decreases to half of the peak current;  
✓Stop baking the prototype | ✓Outgas with the high frequency gun before baking;  
✓Monitor the photo response current, till the increasing trend stops;  
✓Continue baking the prototype at least 2 hours. |